2024년 1월 26일(금), 15:40-17:25
Room J(204),2층

D. Thin Film Process Technology 분과

[FJ3-D] Thin Film Transistors - II

좌장: 이웅규 교수(숭실대학교), 백인환 교수(인하대학교)

FJ3-D-1 15:40-15:55	Role of Post-annealing in Transistors with Oxide Channel/High-k Dielectric Stacks for 3D Stackable Memory Applications Nayeon Kim, Hyunwook Kim, Eunryeong Hong, Seonuk Jeon, and Jiyong Woo School of Electronic and Electrical Engineering, Kyungpook National University
FJ3-D-2 15:55-16:10	Impact of Channel and Blocking Layers for Fast-Speed and Low-Power Operations of Vertical Charge-Trap Memory Using InGaZnO Channel Yun-Ju Cho[1], Young-Ha Kwon[2], Nak-Jin Seong[2], Kyu-Jeong Choi[2], Hee-Ok Kim[3], Jong-Heon Yang[3], Chi-Sun Hwang[3], and Sung-Min Yoon[1] [1]Kyung Hee University, [2]NCD Co., Ltd., [3]ETRI
FJ3-D-3 16:10-16:25	Asymmetrical Self Heating Behavior of Vertical Thin-Film Transistors with Different Source and Drain Electrode Configuration Dong-Hee Lee[1], Young-Ha Kwon[2], Nak-Jin Seong[2], Kyu-Jeong Choi[2], and Sung-Min Yoon[1] [1]Kyung Hee University, [2]NCD Co., Ltd.
FJ3-D-4 16:25-16:40	Effect of Source/Drain Metal-dependent Oxygen Scavenging on the Density of States and Lateral Profile of Carrier Concentration in InGaZnO TFTs Seungki Kim, Wonjung Kim, Changwook Kim, Dong Myong Kim, Sung-Jin Choi, Jong-Ho Bae, and Dae Hwan Kim School of Electrical Engineering, Kookmin University
FJ3-D-5 16:40-16:55	Comparative Analysis of Zinc-Tin-Oxide Films Grown by Atomic Layer Deposition by Varying Chemical Composition Ratio for Improved TFT Performance Dong-Hyun Lim[1], Ae-Rim Choi[2], Yi-Ji Jeong[1], Young-Bae Ahn[3], Seung-Wook Ryu[3], Do-Hee Kim[3], and Il-Kwon Oh[1,2] [1]Department of Electrical and Computer Engineering, Ajou University, [2]Department of Intelligence Semiconductor Engineering, Ajou University, [3]Revolutionary Technology Center, R&D Division, SK hynix

FJ3-D-6 16:55-17:10	Intrinsic Device Characteristics of Oxide TFT with Morphotropic Phase Boundary High-κ Gate Insulator by Fast ID-VG Measurement Taeseung Jung and Sanghun Jeon School of Electrical Engineering, KAIST
FJ3-D-7 17:10-17:25	Improved MOSFETs Performance and Reliability by Low-temperature Deuterium Annealing Ju-Won Yeon, Tae-Hyun Kil, Hyo-Jun Park, and Jun-Young Park Chungbuk National University